CY62147EV30 MoBL®

4-Mbit (256K × 16) Static RAM

Features

- Very high speed: 45 ns
- Temperature ranges
  - Industrial: –40 °C to +85 °C
- Wide voltage range: 2.20 V to 3.60 V
- Pin compatible with CY62147DV30
- Ultra low standby power
  - Typical standby current: 1 µA
  - Maximum standby current: 7 µA (Industrial)
- Ultra low active power
  - Typical active current: 2 mA at f = 1 MHz
- Easy memory expansion with $\overline{CE}$ [1] and $\overline{OE}$ features
- Automatic power-down when deselected
- Complementary metal oxide semiconductor (CMOS) for optimum speed and power
- Available in Pb-free 48-ball very fine ball grid array (VFBGA) (single/dual CE option) and 44-pin thin small outline package (TSOP) II packages
- Byte power-down feature

Functional Description

The CY62147EV30 is a high performance CMOS static RAM (SRAM) organized as 256K words by 16 bits. This device features advanced circuit design to provide ultra low active current. It is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power down feature that significantly reduces power consumption when addresses are not toggling. Placing the device into standby mode reduces power consumption by more than 99 percent when deselected ($\overline{CE}$ HIGH or both $\overline{BLE}$ and $\overline{BHE}$ are HIGH). The input and output pins (I/O_0 through I/O_{15}) are placed in a high impedance state when:

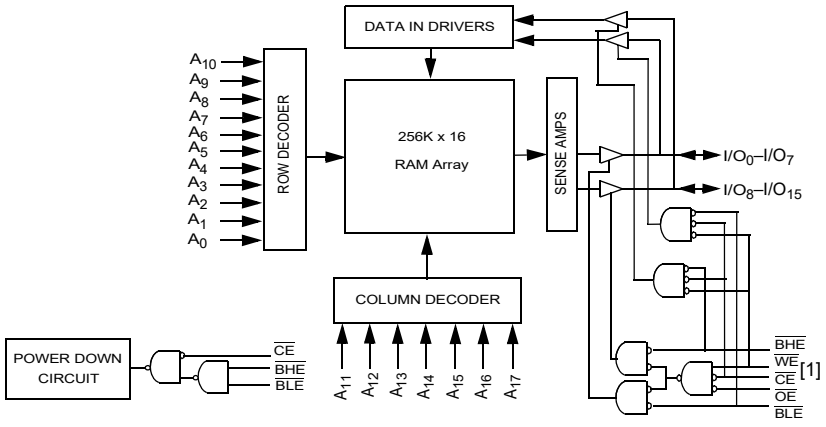
- Deselected ($\overline{CE}$ HIGH)
- Outputs are disabled ($\overline{OE}$ HIGH)
- Both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH)
- Write operation is active ($\overline{CE}$ LOW and $\overline{WE}$ LOW)

To write to the device, take Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7) is written into the location specified on the address pins (A_0 through A_{17}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{17}).

To read from the device, take Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins appear on I/O_0 to I/O_7. If Byte High enable ($\overline{BHE}$) is LOW, then data from memory appears on I/O_8 to I/O_{15}. See the Truth Table on page 11 for a complete description of read and write modes.

For a complete list of related documentation, click here.

Logic Block Diagram



Note

1. BGA packaged device is offered in single CE and dual CE options. In this data sheet, for a dual CE device, $\overline{CE}$ refers to the internal logical combination of $\overline{CE_1}$ and CE_2 such that when $\overline{CE_1}$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW. For all other cases $\overline{CE}$ is HIGH.

Contents

Product Portfolio

Product	Range	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
						Operating I_{CC} (mA)				Standby I_{SB2} (µA)	
						f = 1 MHz		f = f_{max}			
		Min	Typ [2]	Max		Typ [2]	Max	Typ [2]	Max	Typ [2]	Max
CY62147EV30LL	Industrial	2.2	3.0	3.6	45	2	2.5	15	20	1	7

Pin Configurations

Figure 1. 48-ball VFBGA pinout (Single Chip Enable) [3, 4]

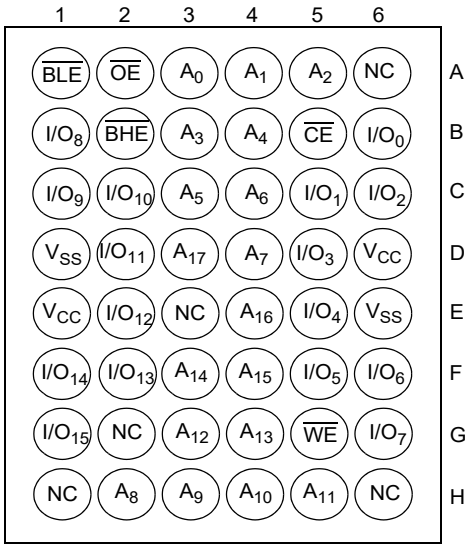


Figure 2. 48-ball VFBGA pinout (Dual Chip Enable) [3, 4]

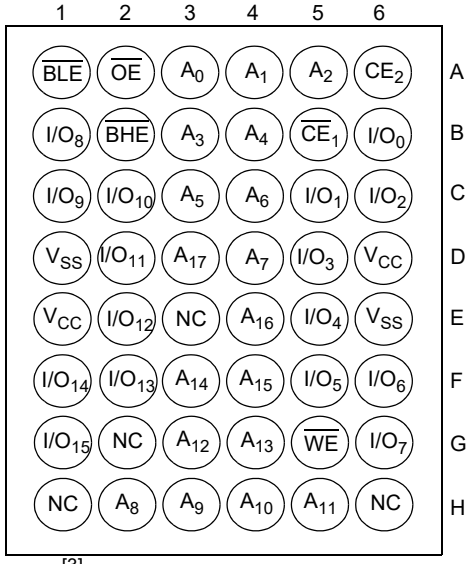
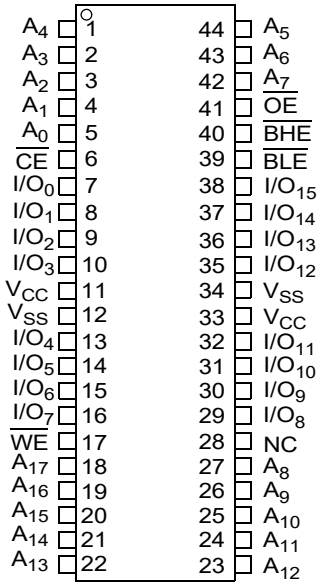


Figure 3. 44-pin TSOP II pinout [3]



Notes
2. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, T_A = 25 °C.
3. NC pins are not connected on the die.
4. Pins H1, G2, and H6 in the BGA package are address expansion pins for 8Mb, 16Mb, and 32Mb, respectively.

Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. User guidelines are not tested.

Storage temperature ..... –65 °C to + 150 °C

Ambient temperature with power applied ..... –55 °C to +125 °C

Supply voltage to ground potential .....–0.3 V to + 3.9 V ($V_{CC(max)}$ + 0.3 V)

DC voltage applied to outputs in High Z state [5, 6] .....–0.3 V to 3.9 V ($V_{CC(max)}$ + 0.3 V)

DC input voltage [5, 6] .....–0.3 V to 3.9 V ($V_{CC(max)}$ + 0.3 V)

Output current into outputs (LOW) ..... 20 mA

Static discharge voltage (MIL-STD-883, method 3015) ..... > 2001 V

Latch-up current .....> 200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC} [7]
CY62147EV30LL	Industrial	–40 °C to +85 °C	2.2 V to 3.6 V

Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions		45 ns (Industrial)			Unit
				Min	Typ [8]	Max	
V_{OH}	Output HIGH voltage	I_{OH} = –0.1 mA		2.0	–	–	V
		I_{OH} = –1.0 mA, $V_{CC} \geq$ 2.70 V		2.4	–	–	V
V_{OL}	Output LOW voltage	I_{OL} = 0.1 mA		–	–	0.4	V
		I_{OL} = 2.1 mA, V_{CC} = 2.70 V		–	–	0.4	V
V_{IH}	Input HIGH voltage	V_{CC} = 2.2 V to 2.7 V		1.8	–	V_{CC} + 0.3	V
		V_{CC}= 2.7 V to 3.6 V		2.2	–	V_{CC} + 0.3	V
V_{IL}	Input LOW voltage	V_{CC} = 2.2 V to 2.7 V		–0.3	–	0.6	V
		V_{CC}= 2.7 V to 3.6 V		–0.3	–	0.8	V
I_{IX}	Input leakage current	GND ≤ V_I ≤ V_{CC}		–1	–	+1	µA
I_{OZ}	Output leakage current	GND ≤ V_O ≤ V_{CC}, output disabled		–1	–	+1	µA
I_{CC}	V_{CC} operating supply current	f = f_{max} = $1/t_{RC}$	V_{CC} = $V_{CC(max)}$, I_{OUT} = 0 mA CMOS levels	–	15	20	mA
		f = 1 MHz		–	2	2.5	
I_{SB1} [9]	Automatic $\overline{CE}$ power-down current – CMOS inputs	$\overline{CE} \geq V_{CC}$ – 0.2 V, $V_{IN} \geq V_{CC}$ – 0.2 V, $V_{IN} \leq$ 0.2 V, f = f_{max} (address and data only), f = 0 ($\overline{OE}$, $\overline{BHE}$, $\overline{BLE}$ and $\overline{WE}$), V_{CC} = 3.60 V		–	1	7	µA
I_{SB2} [9]	Automatic $\overline{CE}$ power-down current – CMOS inputs	$\overline{CE} \geq V_{CC}$ – 0.2 V, $V_{IN} \geq V_{CC}$ – 0.2 V or $V_{IN} \leq$ 0.2 V, f = 0, V_{CC} = 3.60 V		–	1	7	µA

Notes

5. $V_{IL(min)}$ = –2.0 V for pulse durations less than 20 ns.
6. $V_{IH(max)}$ = V_{CC} + 0.75 V for pulse durations less than 20 ns.
7. Full device AC operation assumes a minimum of 100 µs ramp time from 0 to $V_{CC(min)}$ and 200 µs wait time after V_{CC} stabilization.
8. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = $V_{CC(typ)}$, T_A = 25 °C.
9. Chip enable ($\overline{CE}$) and byte enables ($\overline{BHE}$ and $\overline{BLE}$) need to be tied to CMOS levels to meet the I_{SB1} / I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.

Capacitance

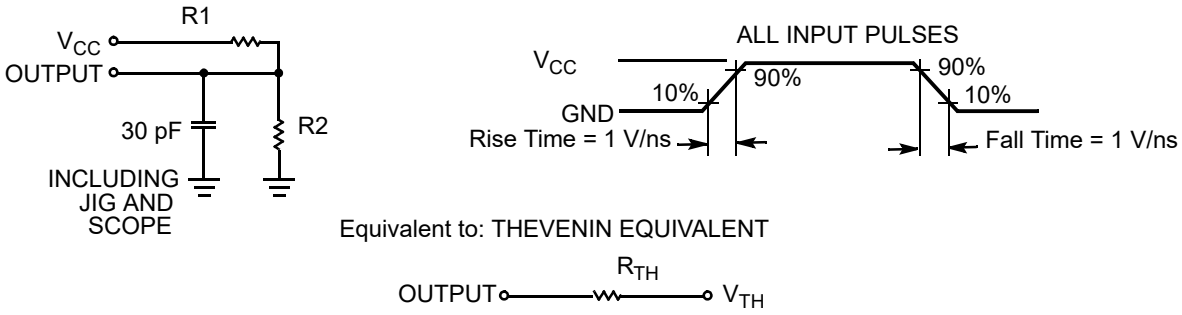
Parameter [10]	Description	Test Conditions	Max	Unit
C_{IN}	Input capacitance	T_A = 25 °C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	10	pF
C_{OUT}	Output capacitance		10	pF

Thermal Resistance

Parameter [10]	Description	Test Conditions	48-ball VFBGA Package	44-pin TSOP II Package	Unit
Θ_{JA}	Thermal resistance (junction to ambient)	Still Air, soldered on a 3 × 4.5 inch, two-layer printed circuit board	42.10	55.52	°C/W
Θ_{JC}	Thermal resistance (junction to case)		23.45	16.03	°C/W

AC Test Load and Waveforms

Figure 4. AC Test Load and Waveforms



Parameters	2.50 V	3.0 V	Unit
R1	16667	1103	Ω
R2	15385	1554	Ω
R_{TH}	8000	645	Ω
V_{TH}	1.20	1.75	V

Note
10. Tested initially and after any design or process changes that may affect these parameters.

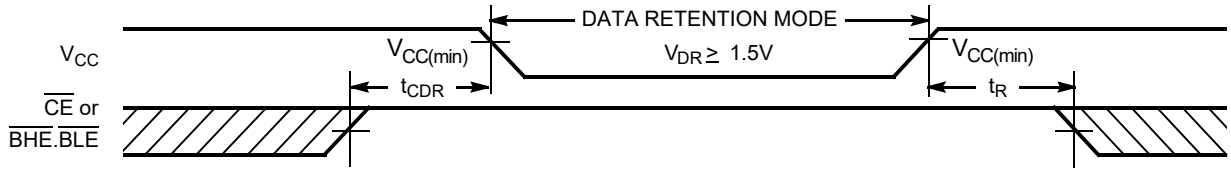
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min	Typ [11]	Max	Unit
V_{DR}	V_{CC} for data retention		1.5	–	–	V
I_{CCDR} [12]	Data retention current	V_{CC} = 1.5 V, $\overline{CE} \geq V_{CC} - 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V or $V_{IN} \leq 0.2$ V	–	0.8	7	µA
t_{CDR} [13]	Chip deselect to data retention time		0	–	–	ns
t_R [14]	Operation recovery time		45	–	–	ns

Data Retention Waveform

Figure 5. Data Retention Waveform [15, 16]



Notes

11. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, T_A = 25 °C.
12. Chip enable ($\overline{CE}$) and byte enables ($\overline{BHE}$ and $\overline{BLE}$) need to be tied to CMOS levels to meet the I_{SB1} / I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.
13. Tested initially and after any design or process changes that may affect these parameters.
14. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)} \geq 100$ µs or stable at $V_{CC(min)} \geq 100$ µs.
15. BGA packaged device is offered in single CE and dual CE options. In this data sheet, for a dual CE device, $\overline{CE}$ refers to the internal logical combination of $\overline{CE}_1$ and CE_2 such that when $\overline{CE}_1$ is LOW and CE_2 is HIGH, CE is LOW. For all other cases CE is HIGH.
16. $\overline{BHE}.\overline{BLE}$ is the AND of both $\overline{BHE}$ and $\overline{BLE}$. Deselect the chip by either disabling the chip enable signals or by disabling both $\overline{BHE}$ and $\overline{BLE}$.

Switching Characteristics

Over the Operating Range

Parameter [17, 18]	Description	45 ns (Industrial)		Unit
		Min	Max	
Read Cycle				
t_{RC}	Read cycle time	45	–	ns
t_{AA}	Address to data valid	–	45	ns
t_{OHA}	Data hold from address change	10	–	ns
t_{ACE}	$\overline{CE}$ LOW to data valid	–	45	ns
t_{DOE}	$\overline{OE}$ LOW to data valid	–	22	ns
t_{LZOE}	$\overline{OE}$ LOW to low Z [19]	5	–	ns
t_{HZOE}	$\overline{OE}$ HIGH to high Z [19, 20]	–	18	ns
t_{LZCE}	$\overline{CE}$ LOW to low Z [19]	10	–	ns
t_{HZCE}	$\overline{CE}$ HIGH to high Z [19, 20]	–	18	ns
t_{PU}	$\overline{CE}$ LOW to power-up	0	–	ns
t_{PD}	$\overline{CE}$ HIGH to power-down	–	45	ns
t_{DBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to data valid	–	45	ns
t_{LZBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to low Z [19, 21]	5	–	ns
t_{HZBE}	$\overline{BLE}$/$\overline{BHE}$ HIGH to high Z [19, 20]	–	18	ns
Write Cycle [22, 23]				
t_{WC}	Write cycle time	45	–	ns
t_{SCE}	$\overline{CE}$ LOW to write end	35	–	ns
t_{AW}	Address setup to write end	35	–	ns
t_{HA}	Address hold from write end	0	–	ns
t_{SA}	Address setup to write start	0	–	ns
t_{PWE}	$\overline{WE}$ pulse width	35	–	ns
t_{BW}	$\overline{BLE}$/$\overline{BHE}$ LOW to write end	35	–	ns
t_{SD}	Data setup to write end	25	–	ns
t_{HD}	Data hold from write end	0	–	ns
t_{HZWE}	$\overline{WE}$ LOW to high Z [19, 20]	–	18	ns
t_{LZWE}	$\overline{WE}$ HIGH to low Z [19]	10	–	ns

Notes

17. Test conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns (1V/ns) or less, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0 to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the Figure 4 on page 5.
18. In an earlier revision of this device, under a specific application condition, READ and WRITE operations were limited to switching of the byte enable and/or chip enable signals as described in the Application Notes AN13842 and AN66311. However, the issue has been fixed and in production now, and hence, these Application Notes are no longer applicable. They are available for download on our website as they contain information on the date code of the parts, beyond which the fix has been in production.
19. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
20. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
21. If both byte enables are toggled together, this value is 10 ns.
22. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$, or both = V_{IL}. All signals must be active to initiate a write and any of these signals can terminate a write by going inactive. The data input setup and hold timing must be referenced to the edge of the signal that terminates the write.
23. The minimum write cycle pulse width for Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW) should be equal to the sum of t_{SD} and t_{HZWE}.

Switching Waveforms

Figure 6. Read Cycle No. 1 (Address Transition Controlled) [24, 25]

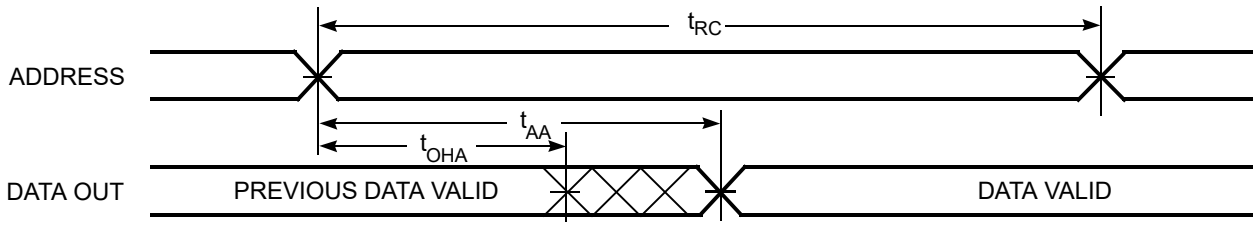
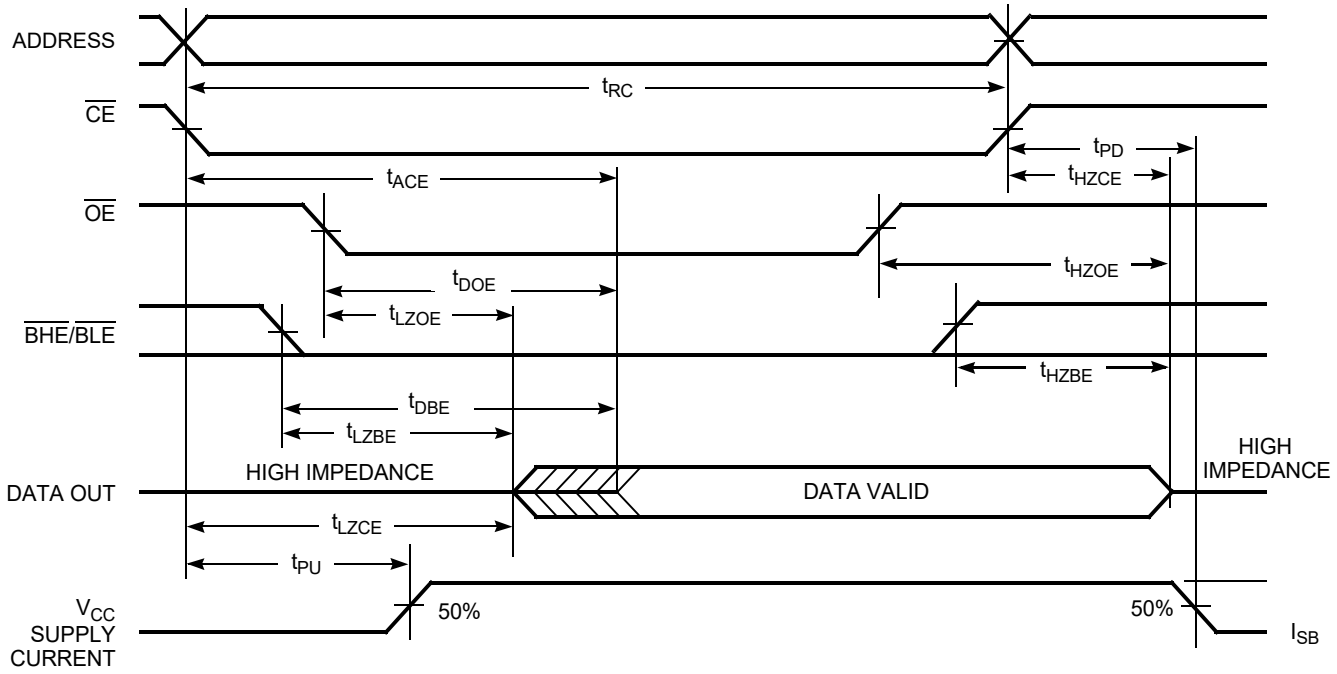


Figure 7. Read Cycle No. 2 ($\overline{OE}$ Controlled) [25, 26, 27]



Notes
24. The device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$, or both = V_{IL}.
25. $\overline{WE}$ is HIGH for read cycle.
26. BGA packaged device is offered in single CE and dual CE options. In this data sheet, for a dual CE device, $\overline{CE}$ refers to the internal logical combination of $\overline{CE}_1$ and CE_2 such that when $\overline{CE}_1$ is LOW and CE_2 is HIGH, CE is LOW. For all other cases CE is HIGH.
27. Address valid before or similar to $\overline{CE}$ and $\overline{BHE}$, $\overline{BLE}$ transition LOW.

Switching Waveforms (continued)

Figure 8. Write Cycle No. 1 ($\overline{WE}$ Controlled) [28, 29, 30, 31]

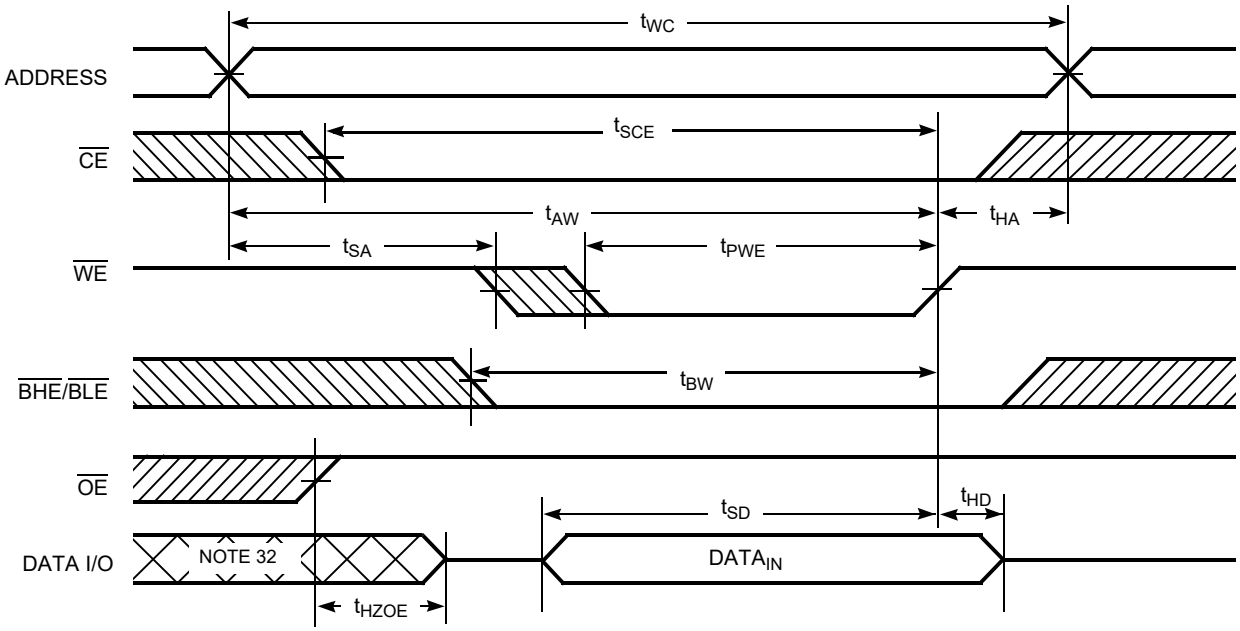
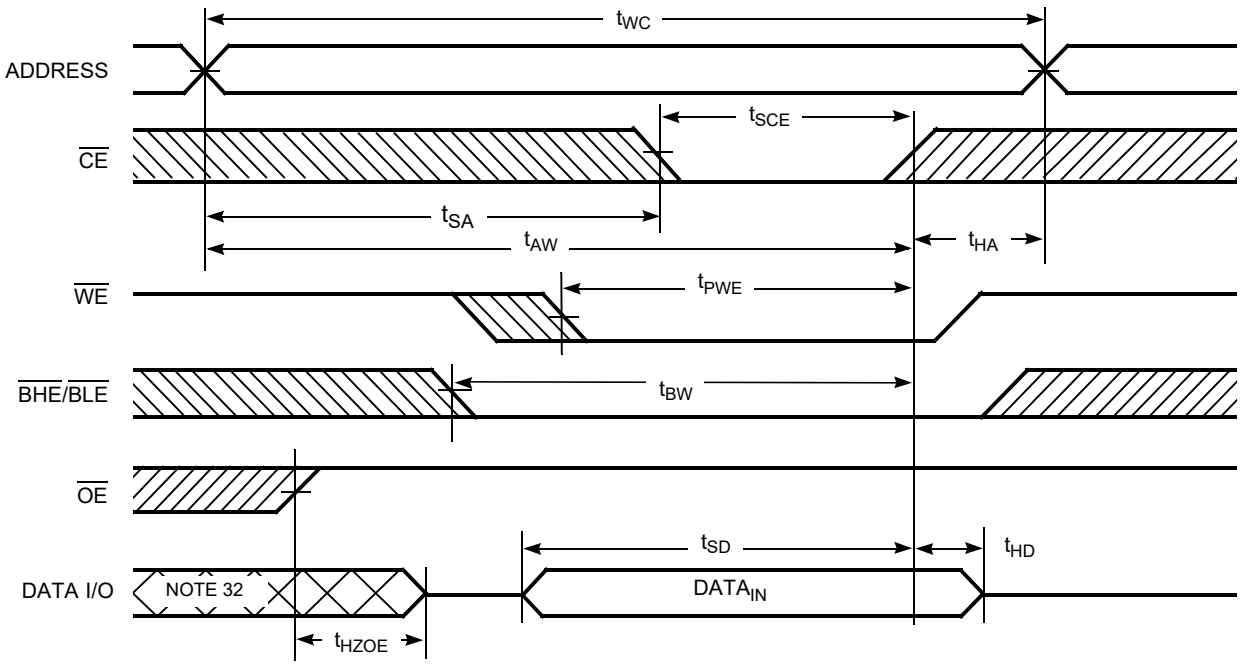


Figure 9. Write Cycle No. 2 ($\overline{CE}$ Controlled) [28, 29, 30, 31]



Notes

28. BGA packaged device is offered in single CE and dual CE options. In this data sheet, for a dual CE device, $\overline{CE}$ refers to the internal logical combination of $\overline{CE_1}$ and CE_2 such that when $\overline{CE_1}$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW. For all other cases $\overline{CE}$ is HIGH.
29. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$, or both = V_{IL}. All signals must be active to initiate a write and any of these signals can terminate a write by going inactive. The data input setup and hold timing must be referenced to the edge of the signal that terminates the write.
30. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
31. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ = V_{IH}, the output remains in a high impedance state.
32. During this period, the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 10. Write Cycle No. 3 (WE Controlled, OE LOW) [33, 34, 35]

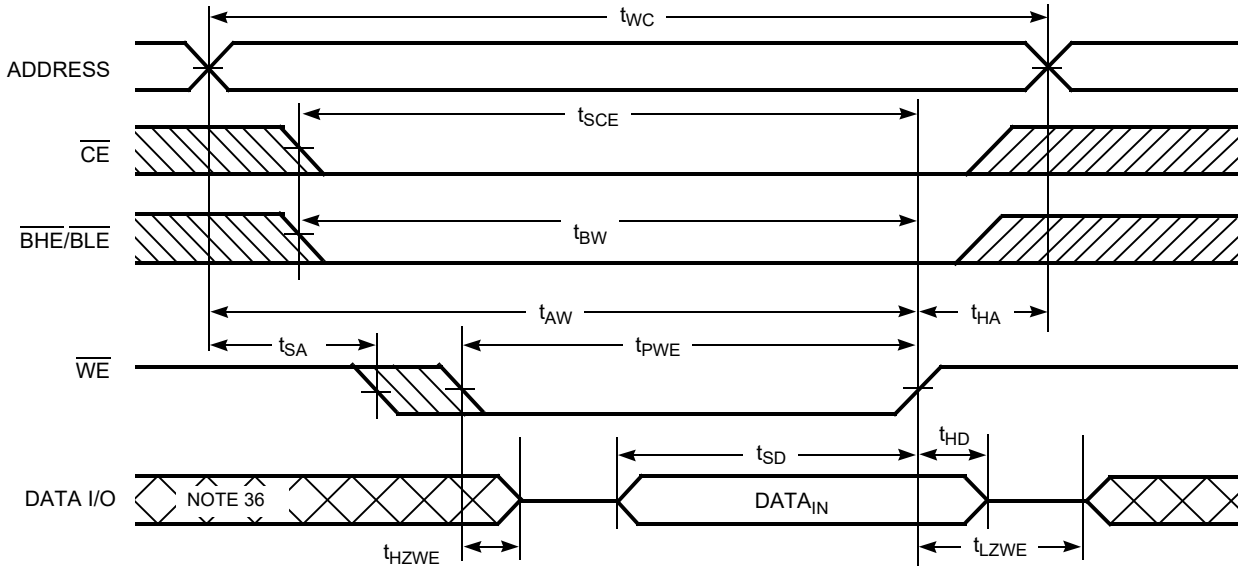
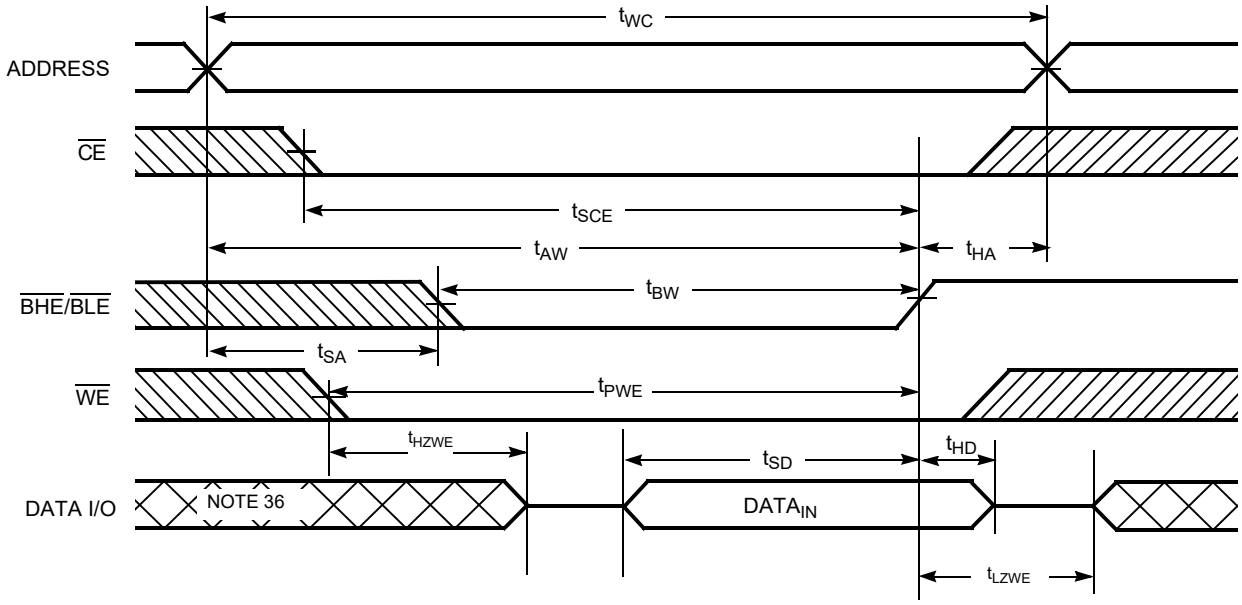


Figure 11. Write Cycle No. 4 (BHE/BLE Controlled) [33, 34]



Notes

33. BGA packaged device is offered in single CE and dual CE options. In this data sheet, for a dual CE device, $\overline{CE}$ refers to the internal logical combination of $\overline{CE}_1$ and CE_2 such that when $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW. For all other cases $\overline{CE}$ is HIGH.
34. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ = V_{IH}, the output remains in a high impedance state.
35. The minimum write cycle pulse width should be equal to the sum of t_{SD} and t_{HZWE}.
36. During this period, the I/Os are in output state. Do not apply input signals.

Truth Table

$\overline{CE}$ [37, 38]	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	I/Os	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
L	X	X	H	H	High Z	Deselect/Power-down	Standby (I_{SB})
L	H	L	L	L	Data out (I/O_0–I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data out (I/O_0–I/O_7); I/O_8–I/O_{15} in High Z	Read	Active (I_{CC})
L	H	L	L	H	Data out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Read	Active (I_{CC})
L	H	H	L	L	High Z	Output disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output disabled	Active (I_{CC})
L	H	H	L	H	High Z	Output disabled	Active (I_{CC})
L	L	X	L	L	Data in (I/O_0–I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data in (I/O_0–I/O_7); I/O_8–I/O_{15} in High Z	Write	Active (I_{CC})
L	L	X	L	H	Data in (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Write	Active (I_{CC})

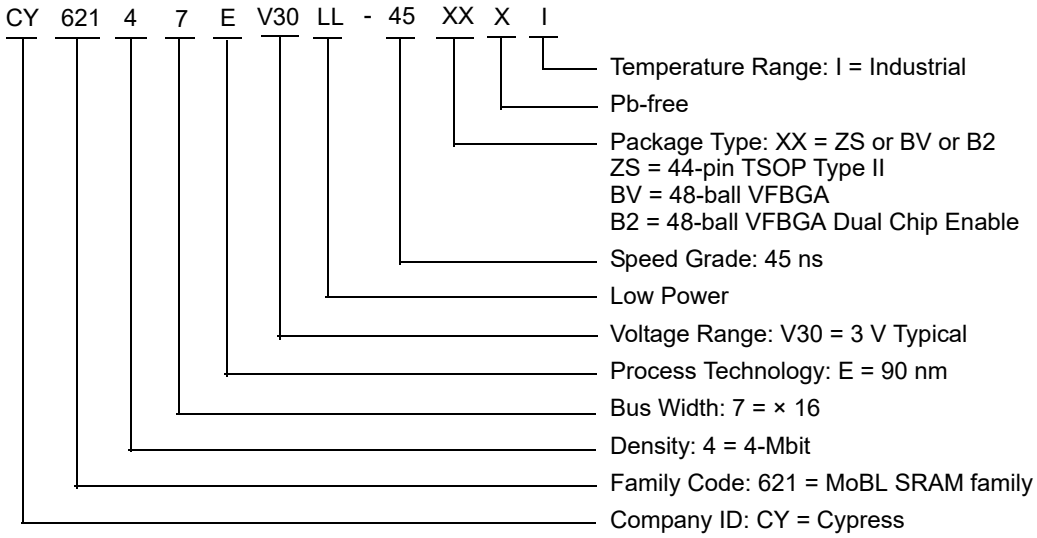
Notes
37. BGA packaged device is offered in single CE and dual CE options. In this data sheet, for a dual CE device, $\overline{CE}$ refers to the internal logical combination of $\overline{CE}_1$ and CE_2 such that when $\overline{CE}_1$ is LOW and CE_2 is HIGH, CE is LOW. For all other cases CE is HIGH.
38. For the Dual Chip Enable device, $\overline{CE}$ refers to the internal logical combination of $\overline{CE}_1$ and CE_2 such that when $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW. For all other cases CE is HIGH. Intermediate voltage levels are not permitted on any of the Chip Enable pins (CE for the Single Chip Enable device; $\overline{CE}_1$ and CE_2 for the Dual Chip Enable device).

Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62147EV30LL-45BVI	51-85150	48-ball VFBGA [39]	Industrial
	CY62147EV30LL-45BVXI	51-85150	48-ball VFBGA (Pb-free) [39]	
	CY62147EV30LL-45B2XI	51-85150	48-ball VFBGA (Pb-free) [40]	
	CY62147EV30LL-45ZSXI	51-85087	44-pin TSOP Type II (Pb-free)	

Contact your local Cypress sales representative for availability of these parts.

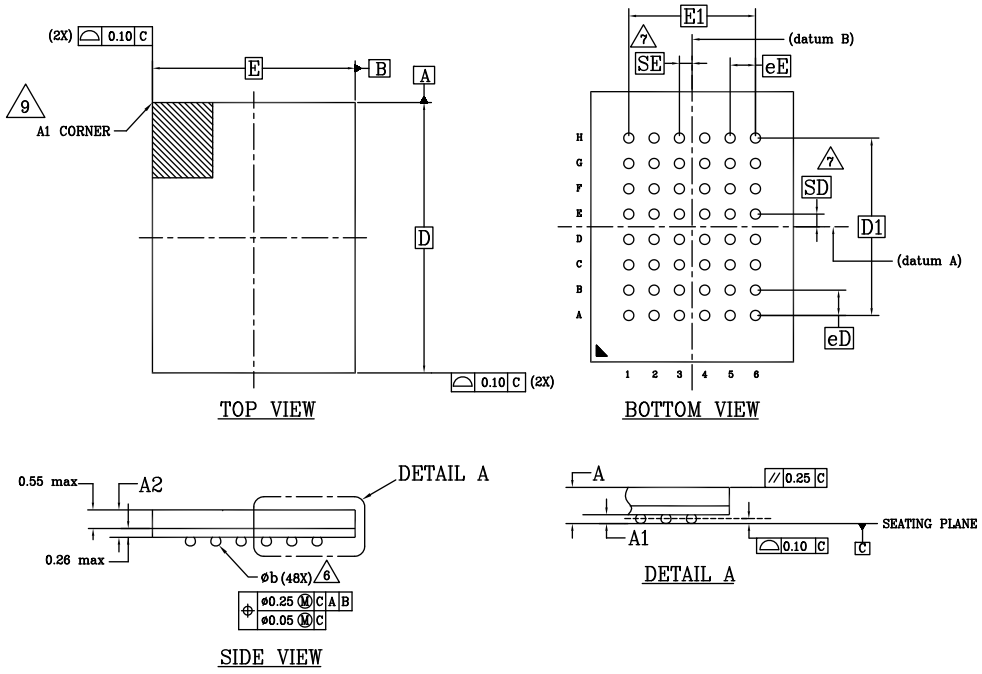
Ordering Code Definitions



Notes
39. This BGA package is offered with single chip enable.
40. This BGA package is offered with dual chip enable.

Package Diagrams

Figure 12. 48-ball VFBGA (6.0 × 8.0 × 1.0 mm) Package Outline, 51-85150



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	-	-	1.00
A1	0.16	-	-
A2	-	-	0.81
D		8.00 BSC	
E		6.00 BSC	
D1		5.25 BSC	
E1		3.75 BSC	
MD		8	
ME		6	
n		48	
Ø b	0.25	0.30	0.35
eE		0.75 BSC	
eD		0.75 BSC	
SD		0.375 BSC	
SE		0.375 BSC	

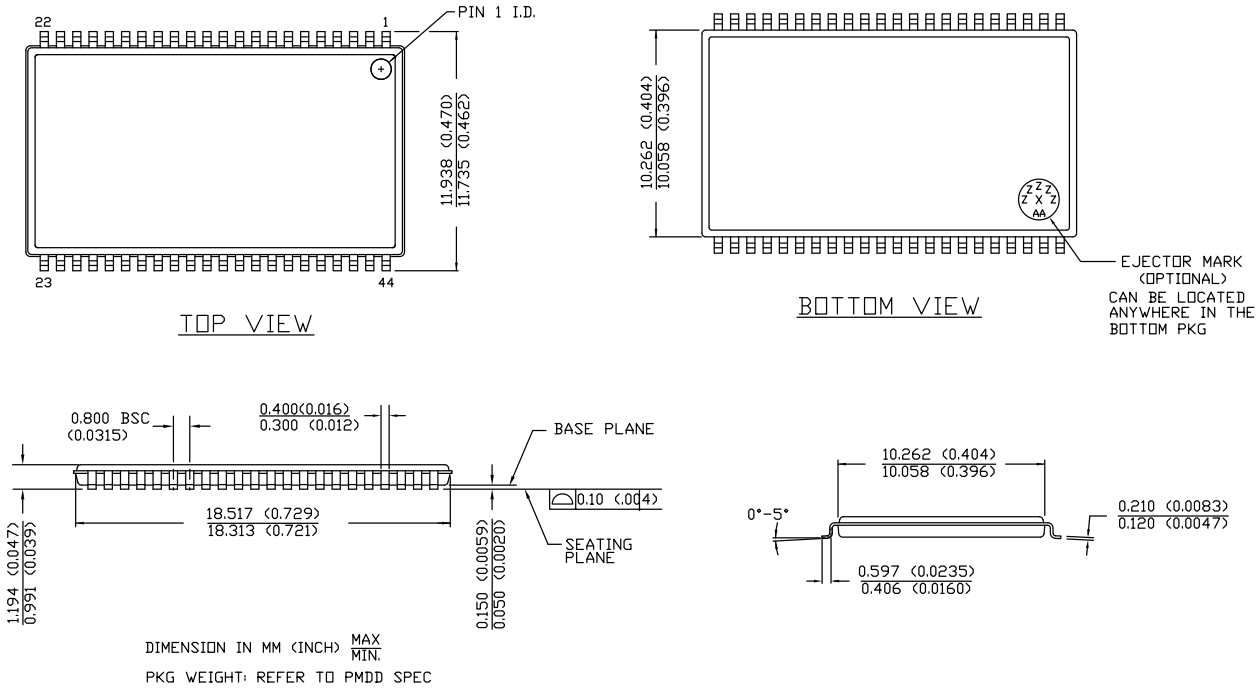
NOTES:

1. DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-2009.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
4. e REPRESENTS THE SOLDER BALL GRID PITCH.
5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.
   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
   n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
6. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
7. "SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW "SD" OR "SE" = 0.
   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" = eD/2 AND "SE" = eE/2.
8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
9. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.

51-85150 *I

Package Diagrams (continued)

Figure 13. 44-pin TSOP II Package Outline, 51-85087



51-85087 *E

Acronyms

Acronym	Description
$\overline{BHE}$	Byte High Enable
$\overline{BLE}$	Byte Low Enable
$\overline{CE}$	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
$\overline{OE}$	Output Enable
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
VFBGA	Very Fine-Pitch Ball Grid Array
$\overline{WE}$	Write Enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
µA	microampere
µs	microsecond
mA	milliampere
ns	nanosecond
Ω	ohm
pF	picofarad
V	volt
W	watt

Document History Page

Document Title: CY62147EV30 MoBL®, 4-Mbit (256K × 16) Static RAM Document Number: 38-05440				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
**	201861	AJU	01/13/2004	New data sheet.
*A	247009	SYT	07/27/2004	Changed status from Advanced Information to Preliminary. Updated Operating Range: Updated Note 7 (Replaced 100 µs with 200 µs). Updated Data Retention Characteristics: Changed maximum value of I_{CCDR} parameter from 2.0 µA to 2.5 µA. Changed minimum value of t_R parameter from 100 µs to t_{RC} ns. Updated Switching Characteristics: Changed minimum value of t_{OHA} parameter from 6 ns to 10 ns corresponding to both 35 ns and 45 ns speed bins. Changed maximum value of t_{DOE} parameter from 15 ns to 18 ns corresponding to 35 ns speed bin. Changed maximum value of t_{HZOE}, t_{HZBE}, t_{HZWE} parameters from 12 ns to 15 ns corresponding to 35 ns speed bin and from 15 ns to 18 ns corresponding to 45 ns speed bin. Changed minimum value of t_{SCE}, t_{BW} parameters from 25 ns to 30 ns corresponding to 35 ns speed bin and from 40 ns to 35 ns corresponding to 45 ns speed bin. Changed maximum value of t_{HZCE} parameter from 12 ns to 18 ns corresponding to 35 ns speed bin and from 15 ns to 22 ns corresponding to 45 ns speed bin. Changed minimum value of t_{SD} parameter from 15 ns to 18 ns corresponding to 35 ns speed bin and from 20 ns to 22 ns corresponding to 45 ns speed bin. Removed Note “If both Byte Enables ($\overline{BHE}$ and $\overline{BLE}$) are toggled together then this value is 6 ns min. Otherwise this value is 3 ns min.” and its reference in t_{LZBE} parameter. Updated Ordering Information: Updated part numbers.
*B	414807	ZSD	12/16/2005	Changed status from Preliminary to Final. Removed 35 ns speed bin related information in all instances across the document. Removed “L” version (of CY62147EV30) related information in all instances across the document. Updated Product Portfolio: Changed typical value of “Operating I_{CC}” from 1.5 mA to 2 mA at “f = 1 MHz”. Changed maximum value of “Operating I_{CC}” from 2 mA to 2.5 mA at “f = 1 MHz”. Changed typical value of “Operating I_{CC}” from 12 mA to 15 mA at “f = f_{max}”. Updated Pin Configurations: Updated figure “48-ball VFBGA pinout” (Replaced DNU with NC in ball E3). Removed Note “DNU pins have to be left floating or tied to V_{SS} to ensure proper application.” and its reference.

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Document Title: CY62147EV30 MoBL®, 4-Mbit (256K × 16) Static RAM Document Number: 38-05440				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
*B (cont.)	414807	ZSD	12/16/2005	Updated Electrical Characteristics: Changed typical value of I_{CC} parameter from 12 mA to 15 mA corresponding to Test Condition "f = f_{max}". Changed typical value of I_{CC} parameter from 1.5 mA to 2 mA corresponding to Test Condition "f = 1 MHz". Changed maximum value of I_{CC} parameter from 2 mA to 2.5 mA corresponding to Test Condition "f = 1 MHz". Changed typical value of I_{SB1}, I_{SB2} parameters from 0.7 µA to 1 µA. Changed maximum value of I_{SB1}, I_{SB2} parameters from 2.5 µA to 7 µA. Updated AC Test Load and Waveforms: Changed AC Test Load Capacitance from 50 pF to 30 pF. Updated Data Retention Characteristics: Added typical value of I_{CCDR} parameter. Changed maximum value of I_{CCDR} parameter from 2.5 µA to 7 µA. Updated Switching Characteristics: Changed minimum value of t_{LZOE} parameter from 3 ns to 5 ns. Changed minimum value of t_{LZCE}, t_{LZBE}, t_{LZWE} parameters from 6 ns to 10 ns. Changed maximum value of t_{HZCE} parameter from 22 ns to 18 ns. Changed minimum value of t_{PWE} parameter from 30 ns to 35 ns. Changed minimum value of t_{SD} parameter from 22 ns to 25 ns. Updated Ordering Information: Updated part numbers. Removed "Package Name" column. Added "Package Diagram" column. Updated Package Diagrams: spec 51-85150 – Changed revision from *B to *D. Updated to new template.
*C	464503	NXR	05/25/2006	Added Automotive-E Temperature Range related information in all instances across the document and assigned Preliminary status (shaded the area) in required places. Added 55 ns speed bin related information in all instances across the document. Updated Ordering Information: Updated part numbers.
*D	925501	VKN	04/09/2007	Added Automotive-A Temperature Range related information in all instances across the document and assigned Preliminary status (shaded the area) in required places. Updated Electrical Characteristics: Added Note 9 and referred the same note in I_{SB2} parameter. Updated Data Retention Characteristics: Added Note 12 and referred the same note in I_{CCDR} parameter. Updated Switching Characteristics: Added Note 18 and referred the same note in "Parameter" column.
*E	1045701	VKN	05/07/2007	Changed status of Automotive-A and Automotive-E Temperature Range related information from Preliminary to Final (unshaded the area).
*F	2577505	VKN / PYRS	10/03/2008	Updated Ordering Information: Updated part numbers. Updated to new template.
*G	2681901	VKN / PYRS	04/01/2009	Updated Ordering Information: Updated part numbers.

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Document Title: CY62147EV30 MoBL®, 4-Mbit (256K × 16) Static RAM Document Number: 38-05440				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
*H	2886488	AJU	03/02/2010	Updated Truth Table: Added Note 38 and referred the same note in "$\overline{CE}$" column. Updated Package Diagrams: spec 51-85150 – Changed revision from *D to *E. spec 51-85087 – Changed revision from *A to *C. Updated to new template.
*I	3109050	PRAS	12/13/2010	Changed Table Footnotes to Notes in all instances across the document. Updated Ordering Information: No change in part numbers. Added Ordering Code Definitions. Updated Package Diagrams: spec 51-85150 – Changed revision from *E to *F.
*J	3123973	RAME	01/31/2011	Removed Automotive-A and Automotive-E Temperature Range related information in all instances across the document. Updated Ordering Information: Updated part numbers. Added Acronyms and Units of Measure.
*K	3296744	RAME	08/09/2011	Updated Functional Description: Updated description. Updated Electrical Characteristics: Updated Note 9. Referred Note 9 in I_{SB1} parameter. Updated Data Retention Characteristics: Updated Note 12. Updated Switching Characteristics: Added Note 21 and referred the same note in the description of t_{LZBE} parameter. Completing Sunset Review.
*L	3456837	TAVA	12/06/2011	Updated Package Diagrams: spec 51-85150 – Changed revision from *F to *G. spec 51-85087 – Changed revision from *C to *D. Updated to new template.
*M	3724736	JISH	08/23/2012	Fixed typo errors. Minor clean-up. Completing Sunset Review.
*N	4102445	VINI	08/22/2013	Updated Switching Characteristics: Updated Note 18. Updated Package Diagrams: spec 51-85150 – Changed revision from *G to *H. spec 51-85087 – Changed revision from *D to *E. Updated to new template. Completing Sunset Review.
*O	4576526	VINI	11/21/2014	Updated Functional Description: Added "For a complete list of related documentation, click here." at the end. Updated Switching Characteristics: Added Note 23 and referred the same note in "Write Cycle". Updated Switching Waveforms: Added Note 35 and referred the same note in Figure 10.
*P	4918858	VINI	09/14/2015	Updated Switching Waveforms: Updated Figure 11 (Updated caption only (Removed "$\overline{OE}$ LOW")). Updated to new template. Completing Sunset Review.

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Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
*Q	5445135	VINI	09/22/2016	Updated Thermal Resistance: Updated values of Θ_{JA} and Θ_{JC} parameters corresponding to all packages. Updated to new template. Completing Sunset Review.
*R	5984537	AESATMP9	12/05/2017	Updated Cypress Logo and Copyright.
*S	6548255	VINI	04/17/2019	Updated Package Diagrams: spec 51-85150 – Changed revision from *H to *I. Updated to new template.

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